II. Amendments to the Specification

Please replace the paragraph beginning at the top of Page 6 under "Description of the Preferred Embodiments" and continuing onto Page 7 with the following amended paragraph:

Fig. 2 depicts a vertical cross section of a multiple element bipolar ESD protection device. The starting structure is a p doped substrate 10, typically created on a silicon wafer of 100 crystal orientation and with a doping level in the range of 10^{15} atoms per cubic centimeter (a/cm^3). A heavily doped n+ first semiconductor layer 12 called a buried layer or subcollector is formed upon the substrate typically using arsenic or antimony as impurity <u>dopants</u> ~~dopents~~ and using either a chemical diffusion or an ion implant process. An ion implant process typically uses an implant energy in the range of 30 KeV with a dosage of 10^{15} atoms per square centimeter (a/cm^2) to produce a n+ buried layer doping level between 10^{18} and 10^{19} a/cm^3. Next, a light to moderately doped n type epitaxial second semiconductor layer 14 is deposited with a doping level typically in the range of 10^{15} to 10^{16} a/cm^3 with arsenic frequently being used as the <u>dopant</u> ~~dopent~~ source element. A plurality of deep n+ regions 16 are implanted into the second semiconductor layer 14 beneath the collector contact regions <u>18</u> typically using either an arsenic, antimony or phosphorous <u>dopant</u> ~~dopent~~ with an implant energy in the range of 30 KeV with a dosage of 10^{15} a/cm^2 to produce an n+ ~~buried layer~~ <u>region</u> doping level between 10^{18} and 10^{19} a/cm^3. This provides a low resistance path to the surface conductor system 34 for the collector current. The structure processing is continued by implanting a third semiconductor layer 24 of p <u>dopant</u> ~~dopent,~~ usually boron, with an implant energy in the range of 30 KeV with a dosage of

10^{14} a/cm^2 to produce a p layer with a typical impurity concentration in a range of between 10^{17} and 10^{18} a/cm^3 to form the transistor base regions. This is followed by implanting a plurality of p+ regions 22 using boron as a source with doping levels typically between 10^{18} and 10^{19} a/cm^3 within the third semiconductor layer base region 24 to form high conductivity regions for the base electrical contacts 20. Next, a plurality of third n doped semiconductor regions 26 is implanted, typically with phosphorous, with an implant energy in the range of 30 KeV and with a dosage of between 10^{16} and 10^{17} a/cm^2 to produce a p layer with a typical impurity concentration in a range of between 10^{19} and 10^{20} a/cm^3 for the transistor emitter regions 26. The electrical contacts with the surface collectors for the collector 18, base 20, and emitter 28 are typically made by using a refractory metal silicide such as titanium silicide (TiSi2) or tungsten silicide ~~(Wsi_2)~~ (WSi_2) together with doped polysilicon (poly) or aluminum conductor elements.

Please replace the last paragraph beginning on line 11 of Page 10 with the following amended paragraph:

What is claimed is: